

Features

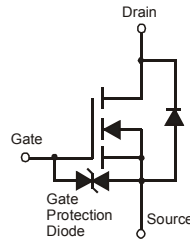
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Up To 2kV**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

Mechanical Data

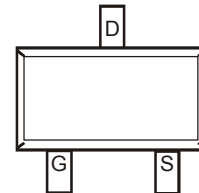
- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish – Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 ^(e3)
- Weight: 0.006 grams (Approximate)



TOP VIEW



EQUIVALENT CIRCUIT



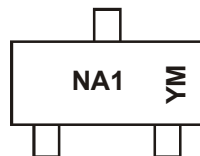
TOP VIEW

Ordering Information (Note 4)

Part Number	Case	Packaging
DMG1012UW-7	SOT323	3000 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



NA1 = Product Type Marking Code
 YM = Date Code Marking
 Y or Ŷ = Year (ex: I = 2021)
 M = Month (ex: 9 = September)

Date Code Key

Year	2009	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	W	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	± 6	V
Continuous Drain Current (Note 5)	Steady State	$T_A = +25^\circ\text{C}$	I_D	1.0	A
		$T_A = +85^\circ\text{C}$		0.64	
Pulsed Drain Current (Note 6)			I_{DM}	6	A

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	P_D	0.29	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 5)	$R_{\theta JA}$	425	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
6. Repetitive rating, pulse width limited by junction temperature.

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	-	-	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	-	-	100	nA	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	-	-	± 1.0	μA	$V_{GS} = \pm 4.5\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	-	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	-	0.3	0.45	Ω	$V_{GS} = 4.5\text{V}, I_D = 600\text{mA}$
			0.4	0.6		$V_{GS} = 2.5\text{V}, I_D = 500\text{mA}$
			0.5	0.75		$V_{GS} = 1.8\text{V}, I_D = 350\text{mA}$
Forward Transfer Admittance	$ Y_{fs} $	-	1.4	-	S	$V_{DS} = 10\text{V}, I_D = 400\text{mA}$
Diode Forward Voltage	V_{SD}	-	0.7	1.2	V	$V_{GS} = 0\text{V}, I_S = 150\text{mA}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	-	60.67	-	pF	$V_{DS} = 16\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	-	9.68	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	5.37	-	pF	
Total Gate Charge	Q_g	-	736.6	-	pC	$V_{GS} = 4.5\text{V}, V_{DS} = 10\text{V}, I_D = 250\text{mA}$
Gate-Source Charge	Q_{gs}	-	93.6	-	pC	
Gate-Drain Charge	Q_{gd}	-	116.6	-	pC	
Turn-On Delay Time	$t_{D(on)}$	-	5.1	-	ns	$V_{DD} = 10\text{V}, V_{GS} = 4.5\text{V}, R_L = 47\Omega, R_G = 10\Omega, I_D = 200\text{mA}$
Turn-On Rise Time	t_R	-	7.4	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	26.7	-	ns	
Turn-Off Fall Time	t_F	-	12.3	-	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

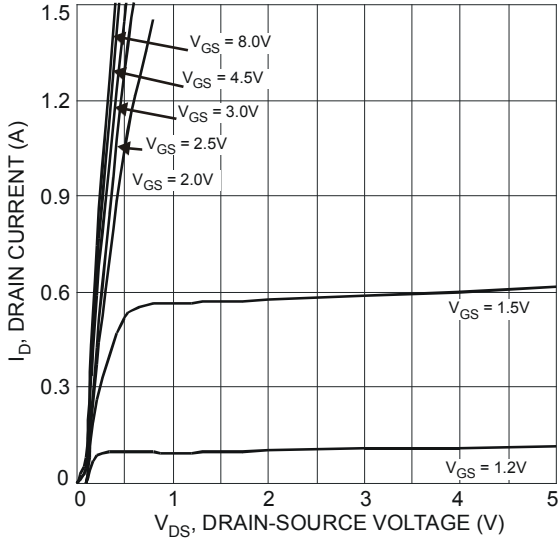


Fig. 1 Typical Output Characteristics

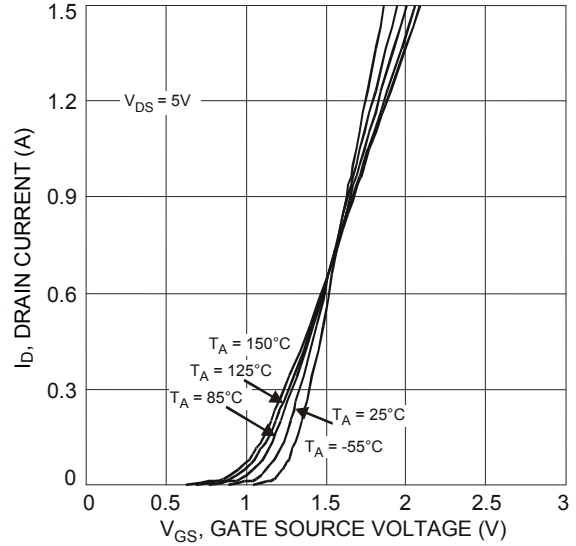


Fig. 2 Typical Transfer Characteristics

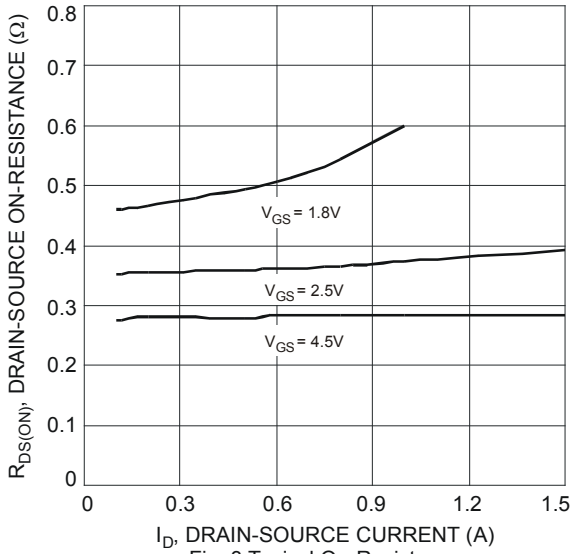


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

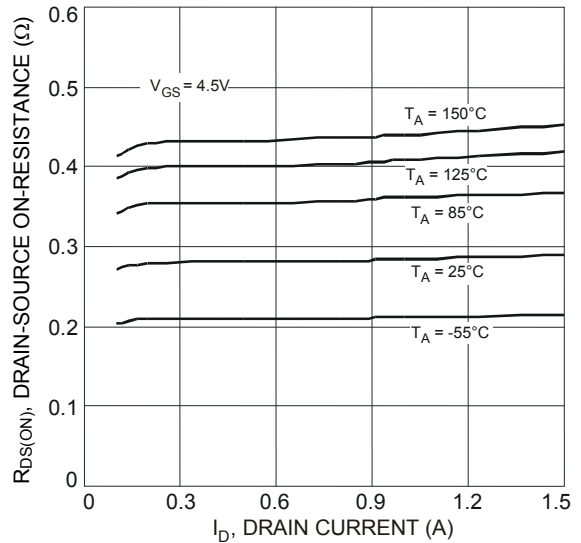


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

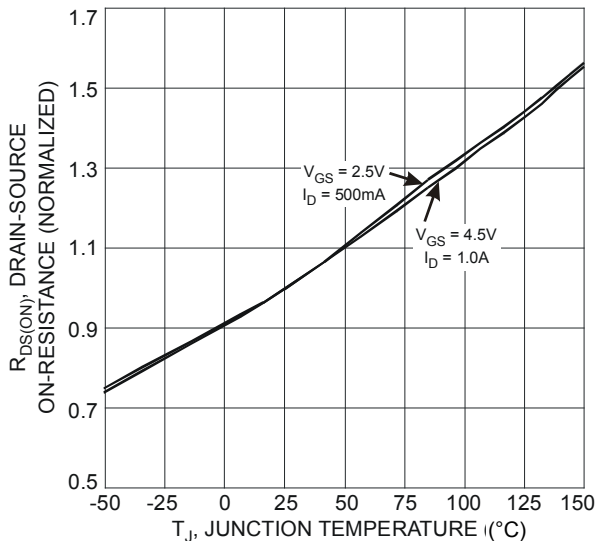


Fig. 5 On-Resistance Variation with Temperature

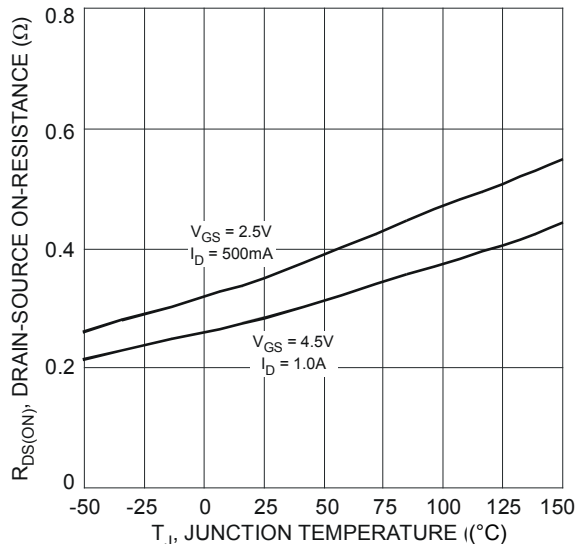


Fig. 6 On-Resistance Variation with Temperature

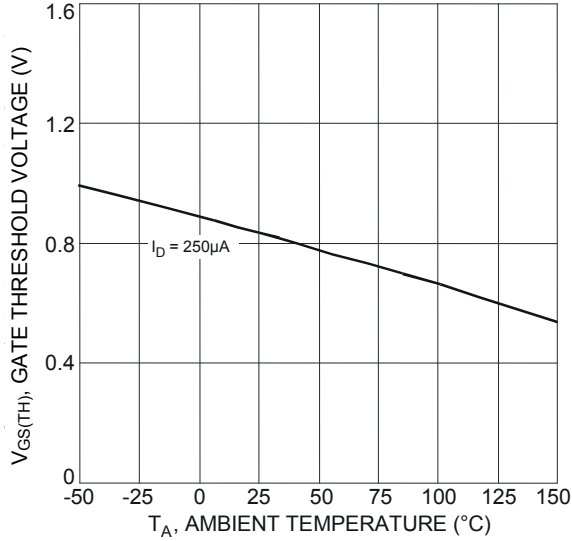


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

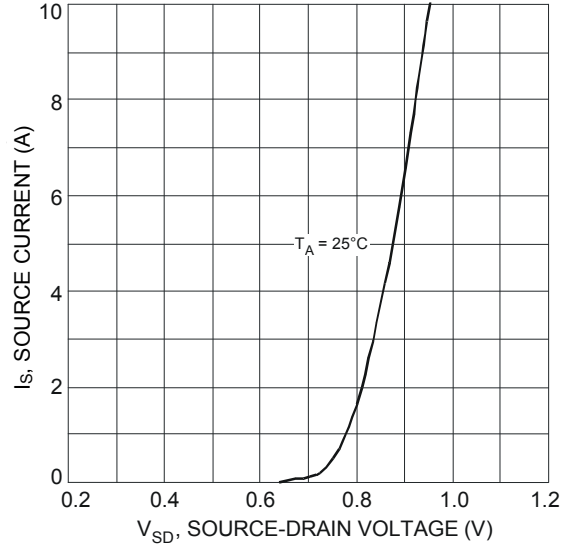


Fig. 8 Diode Forward Voltage vs. Current

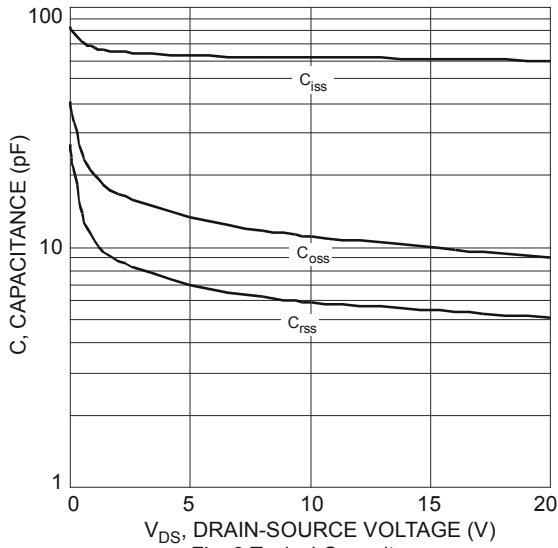


Fig. 9 Typical Capacitance

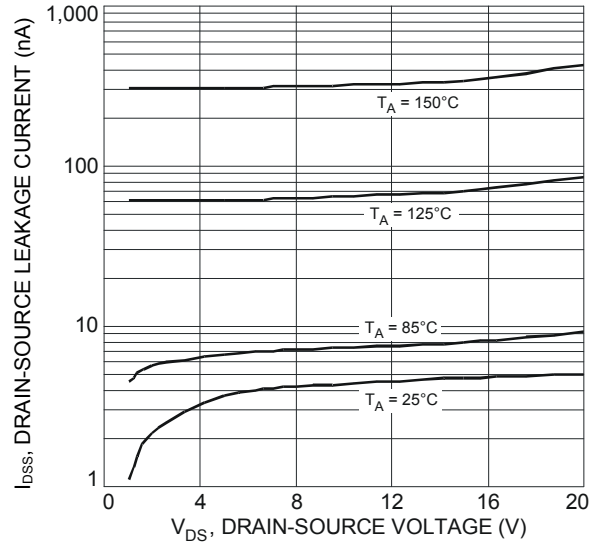


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

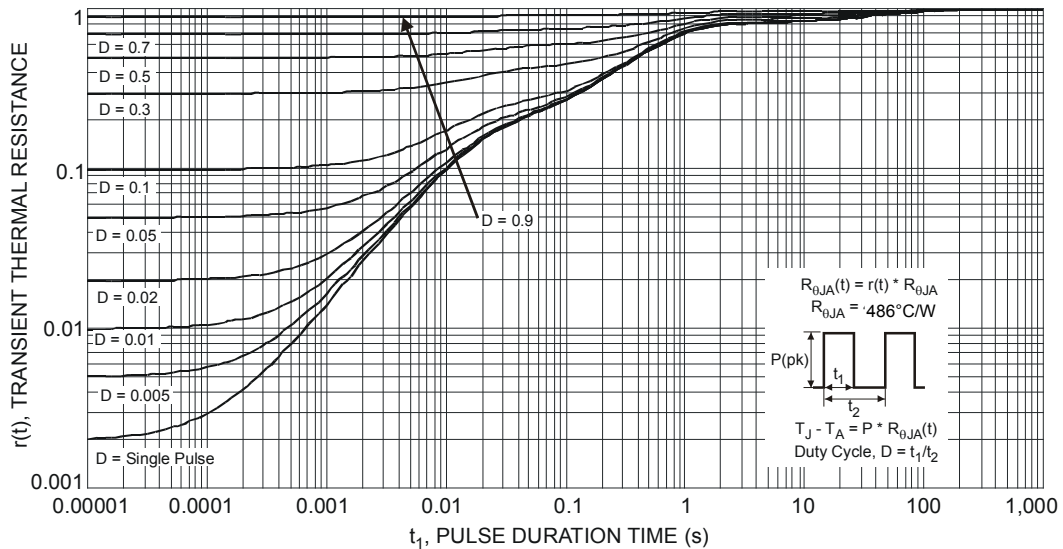
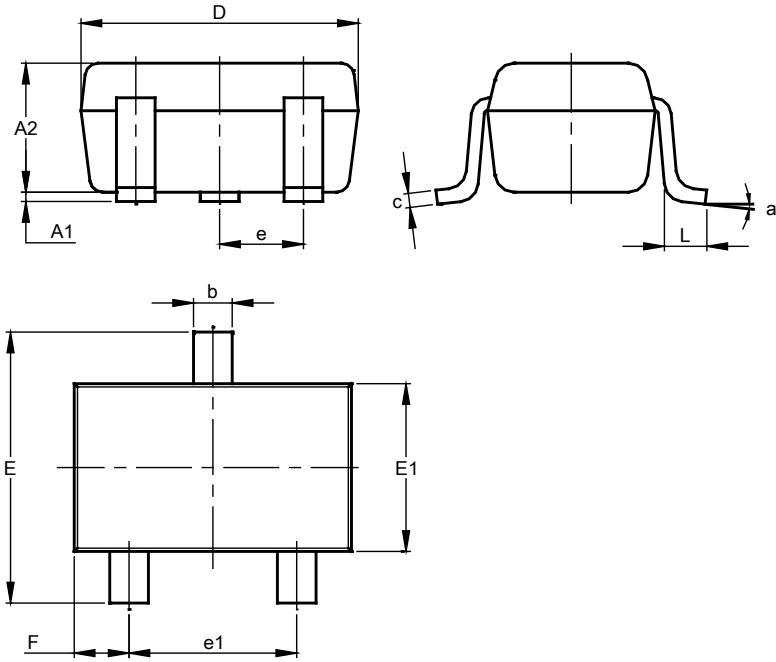


Fig. 11 Transient Thermal Response

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323

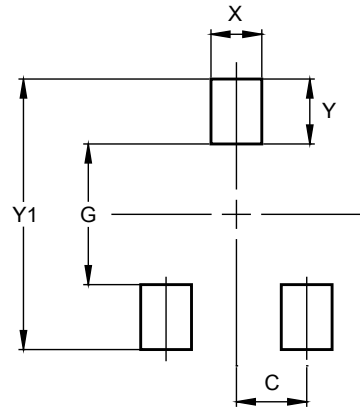


SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.80	1.00	0.90
b	0.20	0.40	0.30
c	0.08	0.18	0.13
D	1.80	2.20	2.00
E	2.00	2.45	2.225
E1	1.15	1.35	1.25
e	--	--	0.65
e1	1.20	1.40	1.30
F	0.25	0.475	0.3625
L	0.25	0.46	0.355
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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